| L | Hit | Sear h Text | DB | Time stamp |
|-------------|-------|-----------------------------|-----------|------------|
| Number - | 1006 | 235/494.ccls. | USPAT; | 2002/05/30 |
| | | | US-P PUB; | 17:55 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 0 | 235/494.ccls. and chiba.in. | USPAT; | 2002/05/30 |
| _ | | - | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 0 | jp-223380-\$.did. | USPAT; | 2002/05/30 |
| _ | |)p-220000-4:aiai | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 9 | "223380" | USPAT; | 2002/05/30 |
| - | | 223300 | US-PGPUB; | |
| | | | EPO; JPO; | 17.07 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 0 | jp-223380-\$.did. | USPAT; | 2002/05/30 |
| - | | jp-223366-\$.uiu. | US-PGPUB; | 17:58 |
| | | | EPO; JPO; | 17.30 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 0 | jp-5923512-\$.did. | USPAT; | 2002/05/30 |
| • | |]p-39233 (2-\$.uiu. | US-PGPUB; | |
| | | | EPO; JPO; | 17.50 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 2 | jp-2000223380-\$.did. | USPAT; | 2002/05/30 |
| - | _ |)p-2000223300-\$.uiu. | US-PGPUB; | 18:00 |
| | | | EPO; JPO; | 10.00 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 0 | jp-2175154-\$.did. | USPAT; | 2002/05/30 |
| _ | | 16 - 110 10-4 Aidigi | US-PGPUB; | 18:00 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 1 | jp-3116919-\$.did. | USPAT; | 2002/05/30 |
| _ | 1 | | US-PGPUB; | 18:00 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 15423 | chiba.in. | USPAT; | 2002/05/30 |
| _ | 13723 | onindilli. | US-PGPUB; | 18:02 |
| | | | EPO; JPO; | 10.02 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 1 | İ | 10111_100 | I |

| | | T | 110000 | 0000/07/07 |
|------------|-------|---|-----------|------------|
| - | 818 | chiba.in. and semiconduct r | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:02 |
| | | | EPO; JPO; | |
| Ì | • | | DERWENT; | |
| | | | IBM_TDB | |
| - | 58 | (chiba.in. and semic nductor) and mark | USPAT; | 2002/05/30 |
| İ | | | US-PGPUB; | 18:05 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| İ | | | IBM_TDB | |
| - | 153 | (chiba.in. and semiconductor) and wafer | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:06 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 83 | 235/494.ccls. and semiconductor | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:10 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 8 | (235/494.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer | US-PGPUB; | 18:06 |
| | | | EPO; JPO; | : |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 34 | (235/494.ccls. and semiconductor) and | USPAT; | 2003/01/09 |
| | | mark | US-PGPUB; | 18:47 |
| |] | | EPO; JPO; | |
| | | | DERWENT; | |
| | • | | IBM_TDB | |
| - | 2 | 6305677.pn. | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:16 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 174 | 269/13.ccls. | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:18 |
| | | · | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 81423 | semiconductor adj2 wafer | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:19 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| 1 | | | IBM_TDB | |
| - | 4744 | (semiconductor adj2 wafer) and mark | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:19 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| L | | | IBM_TDB | |

| | 4500 | // | HEDAT | 2002/05/30 |
|-----|------|--|-----------|------------|
| - | 4500 | ((semi nductor adj2 waf r) and mark) and | USPAT; | |
| | | (semi nduct radj waf r) | US-PGPUB; | 18:20 |
| | 1 | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | 0000/04/00 |
| - | 61 | (((s mic ndu tor adj2 wafer) and mark) and | USPAT; | 2003/01/09 |
| | | (semiconductor adj wafer)) and reproduce | US-PGPUB; | 18:53 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 22 | semiconductor adj mark | USPAT; | 2003/01/09 |
| | | | US-PGPUB; | 18:52 |
| | | | EPO; JPO; | |
| 1 | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 1602 | 355/53.ccls. | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:29 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 1154 | 355/53.ccls. and semiconductor | USPAT; | 2002/05/30 |
| | | | US-PGPUB; | 18:29 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 1052 | (355/53.ccls. and semiconductor) and wafer | USPAT; | 2002/05/30 |
| | | (200.00000 and components) and water | US-PGPUB; | 18:29 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 415 | ((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| - | 7.5 | wafer) and mark | US-PGPUB; | 18:30 |
| | | Water/ und munk | EPO; JPO; | |
| | } | | DERWENT; | |
| | | | IBM_TDB | |
| | 8 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| - | | wafer) and mark) and reproduce | US-PGPUB; | 18:32 |
| | | water, and mark, and reproduce | EPO; JPO; | 13132 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 0 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| 1 - | | wafer) and mark) and efface | US-PGPUB; | 18:32 |
| | | water) and mark) and chace | EPO; JPO; | 10.02 |
| | | | , , | |
| | | | DERWENT; | |
| | _ | ///255/52 colo and comicanductor) and | IBM_TDB | 2002/05/20 |
| - | 5 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and erase | US-PGPUB; | 18:34 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |

| | 0 | (((355/53.ccls. and semiconduct r) and | USPAT; | 2002/05/30 |
|---|-----|--|-----------|---------------------|
| - | | wafer) and mark) and (repr duc adj erased | US-PGPUB; | 18:35 |
| | | adj marks) | EPO; JPO; | 10:33 |
| | | auj marks) | 1 ' ' | |
| | | | DERWENT; | |
| | | (U/255/52 also and a surious duration) and | IBM_TDB | 2002/05/20 |
| - | 0 | ((((355/53. cls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and (reproduce erased | US-PGPUB; | 18:35 |
| | | marks)) and efface | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 10 | ((((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and (reproduce erased | US-PGPUB; | 18:35 |
| | | marks)) and notch | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 300 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and (reproduce erased | US-PGPUB; | 18:38 |
| | | marks) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 0 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and (reproduce near | US-PGPUB; | 18:39 |
| | | erased near marks) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 0 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and (reproduce same | US-PGPUB; | 18:39 |
| | | erased same marks) | EPO; JPO; | |
| | | · | DERWENT; | |
| | | | IBM_TDB | |
| _ | 121 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and identical | US-PGPUB; | 18:40 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 9 | ((((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and identical) and | US-PGPUB; | 18:44 |
| | | reproduce\$2 | EPO; JPO; | |
| | | • | DERWENT; | |
| | | | IBM_TDB | |
| • | 172 | (((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| | ''- | wafer) and mark) and prevent | US-PGPUB; | 18:44 |
| | | water, and main, and pievent | EPO; JPO; | 1-41-4-4 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 3 | ((((355/53.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| - | 3 | wafer) and mark) and prevent) and erase | | 2002/05/30 18:53 |
| | | water, and mark, and prevent, and erase | US-PGPUB; | 10:33 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |

| US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PAT; US-PGPUB; EPO; JPO; | | | | T | |
|---|----|-------|--|-----------|------------|
| - 84 355/43.ccls. and s miconduct r - 84 355/43.ccls. and semiconductor) and wafer - 71 (355/43.ccls. and semiconductor) and wafer - 1 (((355/43.ccls. and semiconductor) and wafer) and mark wafer) and mark - 25968 - 25968 355/\$.ccls. and semiconductor) and wafer - 2416 355/\$.ccls. and semiconductor) and wafer - 25968 ((355/\$.ccls. and semiconductor) and wafer - 2416 355/\$.ccls. and semiconductor) and wafer - 25968 ((355/\$.ccls. and semiconductor) and wafer - | - | 354 | 355/43.ccls. | USPAT; | 2002/05/30 |
| - 84 355/43.ccls. and s miconduct r USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; D | | | | | 18:53 |
| BM_TDB USPAT; USP-GPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USP-GPUB; EPO; JPO; DERWENT; USP-GPUB; USP-GPUB; USP-GPUB; USP | | | | 1 ' | |
| - 25968 355/\$.ccls. and semiconductor) and wafer (((355/\$.ccls. and semiconductor) and wafer wafer) and mark and erase (((355/\$.ccls. and semiconductor) and wafer) uspar; uspaping 2002/05/30 (18:53 (((355/\$.ccls. and semiconductor) and wafer) uspar; uspaping 2002/05/30 (18:53 (((355/\$.ccls. and semiconductor) and wafer) uspar; uspaping 2002/05/30 (18:54 ((((355/\$.ccls. and semiconductor) and wafer) uspar; uspaping 2002/05/30 ((((((((((((((((((((((((((((((((((((| | | | 1 | |
| - 71 (355/43.ccls. and semiconductor) and wafer US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | | | | _ | |
| - 71 (355/43.ccls. and semiconductor) and wafer | - | 84 | 355/43.ccls. and s miconduct r | USPAT; | 2002/05/30 |
| - 1469 (355/\$.ccls. and semiconductor) and wafer | | | | US-PGPUB; | 18:53 |
| - 71 (355/43.ccls. and semiconductor) and wafer USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; E | | | | EPO; JPO; | |
| - 1 ((355/43.ccls. and semiconductor) and wafer USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; E | | | | DERWENT; | |
| US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; ISM_TDB US-AT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; DERWENT; IBM_TDB US-AT; US-PGPUB; EPC; DERWENT; IBM_TD | | | | IBM_TDB | |
| - 45 (((355/43.ccls. and semiconductor) and wafer) and mark) and erase - 45 (((355/43.ccls. and semiconductor) and wafer) and mark - 25968 - 25968 355/\$.ccls. 25968 - 2416 355/\$.ccls. and semiconductor - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) and mark - 497 ((((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((((355/\$.ccls. and semiconductor) and wafer) uspar; uspapels; epo; JPO; Derwent; lbm_TDB uspar; uspapels; epo; JPO; lbm_TDB uspapels; epo; lbm | - | 71 | (355/43.ccls. and semiconductor) and wafer | USPAT; | 2002/05/30 |
| - 45 (((355/43.ccls. and semiconductor) and wafer) and mark) and erase UsPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM | | | | US-PGPUB; | 18:53 |
| - 45 (((355/43.ccls. and semiconductor) and wafer) and mark) and erase UsPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM | | | | EPO; JPO; | |
| 1 | 1 | | | | |
| - 45 (((355/43.ccls. and semiconductor) and wafer) and mark) and erase - 45 (((355/43.ccls. and semiconductor) and wafer) and mark - 25968 (((355/43.ccls. and semiconductor) and wafer) and mark - 25968 ((((355/43.ccls. and semiconductor) and wafer) and mark - 25968 ((((((355/43.ccls. and semiconductor) and wafer) and mark - 25968 ((((((((((((((((((((((((((((((((((((| 1 | | | • | |
| - 45 (((355/43.ccls. and semiconductor) and wafer) and mark - 25968 355/\$.ccls. - 2116 355/\$.ccls. and semiconductor - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) and mark - 497 (((355/\$.ccls. and semiconductor) and wafer) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM | - | 1 | (((355/43.ccls. and semiconductor) and | _ | 2002/05/30 |
| - 45 ((355/43.ccls. and semiconductor) and wafer) wafer) and mark - 25968 355/\$.ccls. - 25968 355/\$.ccls. - 2116 355/\$.ccls. and semiconductor - 1469 (355/\$.ccls. and semiconductor) and wafer - 1470 (355/\$.ccls. and semiconductor) and wafer - 1480 (355/\$.ccls. and semiconductor) and wafer - 1497 (355/\$.ccls. and semiconductor) and wafer - 1497 (355/\$.ccls. and semiconductor) and wafer - 1497 (355/\$.ccls. and semiconductor) and wafer - 1497 (355/\$.ccls. and semiconductor) and wafer - 1497 (355/\$.ccls. and semiconductor) and wafer) - 1497 (355/\$.ccls. and semiconductor) and wafer) - 1497 (355/\$.ccls. and semiconductor) and wafer) - 1497 (355/\$.ccls. and semiconductor) and wafer) - 1497 (355/\$.ccls. and semiconductor) and wafer) - 1497 (355/\$.ccls. and semiconductor) - 1497 (355/\$. | | | | 1 | |
| - 45 ((355/43.ccls. and semiconductor) and wafer) and mark USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US | | | | | , |
| - 45 ((355/43.ccls. and semiconductor) and wafer) and mark - 25968 355/\$.ccls. - 2116 355/\$.ccls. and semiconductor - 1469 (355/\$.ccls. and semiconductor) and wafer - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 497 ((355/\$.ccls. and semiconductor) and wafer) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO | | | | | |
| - 45 ((355/43.ccls. and semiconductor) and wafer) and mark - 25968 355/\$.ccls. - 2116 355/\$.ccls. and semiconductor - 1469 (355/\$.ccls. and semiconductor) and wafer - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 497 ((355/\$.ccls. and semiconductor) and wafer) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; | | | | 1 | |
| - 25968 355/\$.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; ISM_TDB US-PGPUB; EPO; JPO; DERWENT; | 1_ | 45 | ((355/43.ccls. and semiconductor) and | I | 2002/05/30 |
| EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM | | | | | |
| - 25968 355/\$.ccls. DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IBS-59 US-PGP | | | water) and mark | 1 | 10.30 |
| - 25968 355/\$.ccls. IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; | | | | • | |
| - 25968 355/\$.ccls. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US | | | | · . | |
| US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2002/05/30 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; E | | 25069 | 355/\$ colo | _ | 2002/0E/20 |
| - 2116 355/\$.ccls. and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB | - | 25966 | 333/ą.ccis. | · · | |
| - 2116 355/\$.ccls. and semiconductor USPAT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JP | | | | 1 | 10:30 |
| - 2116 355/\$.ccls. and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DE | | | | | |
| - 2116 355/\$.ccls. and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PG | | | | · · | |
| - 1469 (355/\$.ccls. and semiconductor) and wafer - 497 ((355/\$.ccls. and semiconductor) and wafer) - 8 (((355/\$.ccls. and semiconductor) and wafer) and mark - 8 (((355/\$.ccls. and semiconductor) and wafer) wafer) and mark) and erase - 1469 (355/\$.ccls. and semiconductor) and wafer) wafer) and mark - 150 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT; US-PGPUB; EPO; IBM_TDB USPAT | | 2442 | | _ | |
| - 1469 (355/\$.ccls. and semiconductor) and wafer USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 497 ((355/\$.ccls. and semiconductor) and wafer) uSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 8 (((355/\$.ccls. and semiconductor) and wafer) uSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 8 (((355/\$.ccls. and semiconductor) and wafer) uSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 18 (((355/\$.ccls. and semiconductor) and wafer) uSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 19 ((355/\$.ccls. and semiconductor) and wafer) uSPAT; US-PGPUB; EPO; JPO; DERWENT; | - | 2116 | 355/\$.ccis. and semiconductor | 1 ' | |
| - 1469 (355/\$.ccls. and semiconductor) and wafer USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISS-PGPUB; EPO; JPO; DERWENT; ISS-PGPUB; EPO; JPO; DERWENT; | | | | 1 | 18:59 |
| - 1469 (355/\$.ccls. and semiconductor) and wafer USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; | | [| | , , , | |
| - 1469 (355/\$.ccls. and semiconductor) and wafer USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; and mark US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERW | | | | l * 1 | |
| - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 8 (((355/\$.ccls. and semiconductor) and wafer) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 8 (((355/\$.ccls. and semiconductor) and wafer) US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; | | | | _ | |
| - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 8 (((355/\$.ccls. and semiconductor) and wafer) and mark - 8 (((355/\$.ccls. and semiconductor) and wafer) and mark) and erase EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; | - | 1469 | (355/\$.ccls. and semiconductor) and wafer | | |
| - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 8 (((355/\$.ccls. and semiconductor) and wafer) DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; | | | | · . | 18:59 |
| - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 8 (((355/\$.ccls. and semiconductor) and wafer) DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; | | | | 1 | |
| - 497 ((355/\$.ccls. and semiconductor) and wafer) and mark - 8 (((355/\$.ccls. and semiconductor) and wafer) DERWENT; Wafer) and mark) and erase - 18 (((355/\$.ccls. and semiconductor) and Wafer) Wafer) and mark) and erase - 19 ((355/\$.ccls. and semiconductor) and Wafer) Wafer) and Wafer) and Wafer) Bero; JPO; DERWENT; | | | | • | |
| and mark US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; Wafer) and mark) and erase US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; | | | | _ | |
| - 8 (((355/\$.ccls. and semiconductor) and USPAT; Vafer) and mark) and erase US-PGPUB; EPO; JPO; DERWENT; DERWENT; | - | 497 | , , | , , | |
| - 8 (((355/\$.ccls. and semiconductor) and USPAT; 2002/05/30 wafer) and mark) and erase US-PGPUB; EPO; JPO; DERWENT; | | | and mark | ' | 18:59 |
| - 8 (((355/\$.ccls. and semiconductor) and USPAT; 2002/05/30 us-PGPUB; EPO; JPO; DERWENT; | | [| | EPO; JPO; | |
| - 8 (((355/\$.ccls. and semiconductor) and USPAT; 2002/05/30 us-PGPUB; EPO; JPO; DERWENT; | | | | DERWENT; | |
| wafer) and mark) and erase US-PGPUB; EPO; JPO; DERWENT; | | | | IBM_TDB | |
| EPO; JPO; DERWENT; | - | 8 | (((355/\$.ccls. and semiconductor) and | USPAT; | 2002/05/30 |
| DERWENT; | | | wafer) and mark) and erase | US-PGPUB; | 18:59 |
| DERWENT; | | | | EPO; JPO; | |
| | | | | | |
| | | | | IBM_TDB | |

| | 1 | | T | |
|---|----|--|-----------|------------|
| - | 13 | (((355/\$.ccls. and semi ndu t r) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and r pr duce | US-PGPUB; | 19:02 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 1 | ((((355/\$. cls. and semic nduct r) and | USPAT; | 2002/05/30 |
| | | wafer) and mark) and erase) and | US-PGPUB; | 19:02 |
| | | ((((355/\$.ccls. and semiconductor) and | EPO; JPO; | |
| | | wafer) and mark) and reproduce) | DERWENT; | |
| | | | IBM_TDB | |
| - | 6 | (235/494.ccls. and semiconductor) and | USPAT; | 2003/01/09 |
| | | mark and duplicate | US-PGPUB; | 18:51 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 0 | (235/494.ccls. and semiconductor) and | USPAT; | 2003/01/09 |
| | | (duplicate adj mark) | US-PGPUB; | 18:51 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 3 | (235/494.ccls. and semiconductor) and | USPAT; | 2003/01/09 |
| | | (duplicate same mark) | US-PGPUB; | 18:51 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | O | (semiconductor adj mark) same duplicate | USPAT; | 2003/01/09 |
| | | | US-PGPUB; | 18:53 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 0 | ((((semiconductor adj2 wafer) and mark) | USPAT; | 2003/01/09 |
| | | and (semiconductor adj wafer)) and | US-PGPUB; | 18:53 |
| | | reproduce) and (duplicate same mark) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 0 | ((((semiconductor adj2 wafer) and mark) | USPAT; | 2003/01/09 |
| | | and (semiconductor adj wafer)) and | US-PGPUB; | 18:53 |
| | | reproduce) and (duplicate near mark) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 0 | ((((semiconductor adj2 wafer) and mark) | USPAT; | 2003/01/09 |
| | | and (semiconductor adj wafer)) and | US-PGPUB; | 18:53 |
| | | reproduce) and (duplicate adj mark) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 72 | (((semiconductor adj2 wafer) and mark) and | USPAT; | 2003/01/09 |
| | | (semiconductor adj wafer)) and reproduce | US-PGPUB; | 18:54 |
|] | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |

| | 3 | ((((semiconduct radj2 waf r) and mark) | USPAT; | 2003/01/09 |
|----------|-------|--|-----------|------------|
| | | and (semiconduct radj wafer)) and | US-PGPUB; | 18:54 |
| | | repr duce) and duplicate | EPO; JPO; | |
| | | , , , , , , , | DERWENT; | |
| | | | IBM_TDB | |
| ١. | 26645 | 355/\$. Is. | USPAT; | 2003/01/10 |
| | 200-0 | | US-PGPUB; | 12:08 |
| | | | EPO; JPO; | .2.00 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | 102 | 430/13.ccls. | USPAT; | 2003/01/10 |
| - | 102 | 450/15.0015. | US-PGPUB; | 12:09 |
| | | | ' | 12:09 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | 405 | 077/000 | IBM_TDB | 0003/04/40 |
| • | 435 | 257/620.ccls. | USPAT; | 2003/01/10 |
| | | | US-PGPUB; | 12:09 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 1104 | 235/494.ccls. | USPAT; | 2003/05/30 |
| | | | US-PGPUB; | 12:08 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 27013 | 355/\$.ccls. | USPAT; | 2003/05/30 |
| 1 | | | US-PGPUB; | 12:08 |
| 1 | | , | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 462 | 257/620.ccls. | USPAT; | 2003/05/30 |
| | İ | | US-PGPUB; | 12:09 |
| ļ | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| • | 104 | 430/13.ccls. | USPAT; | 2003/05/30 |
| | | | US-PGPUB; | 12:09 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 1015 | replace same mark | USPAT; | 2003/05/30 |
| | | | US-PGPUB; | 12:09 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 99 | (replace same mark) and semiconductor | USPAT; | 2003/05/30 |
| | | | US-PGPUB; | 12:12 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |

| - | 3 | ((replace same mark) and semic nductor) | USPAT; | 2003/05/30 |
|---|-------|--|-----------|------------|
| | | and 235/\$.ccls. | US-PGPUB; | 12:14 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 89611 | semicondu tor adj wafer | USPAT; | 2003/05/30 |
| | | - | US-PGPUB; | 12:19 |
| | | | EPO; JPO; | |
| | ŀ | | DERWENT; | |
| | | | IBM_TDB | |
| - | 5456 | (semiconductor adj wafer) and mark | USPAT; | 2003/05/30 |
| | | | US-PGPUB; | 12:20 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 2 | ((semiconductor adj wafer) and mark) and | USPAT; | 2003/05/30 |
| | | (replace near10 mark) | US-PGPUB; | 12:20 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |